Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

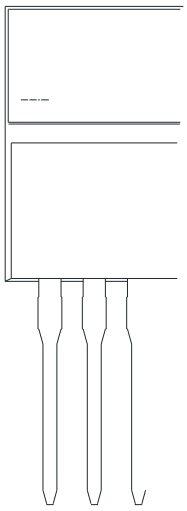
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA

ORDERING INFORMATION

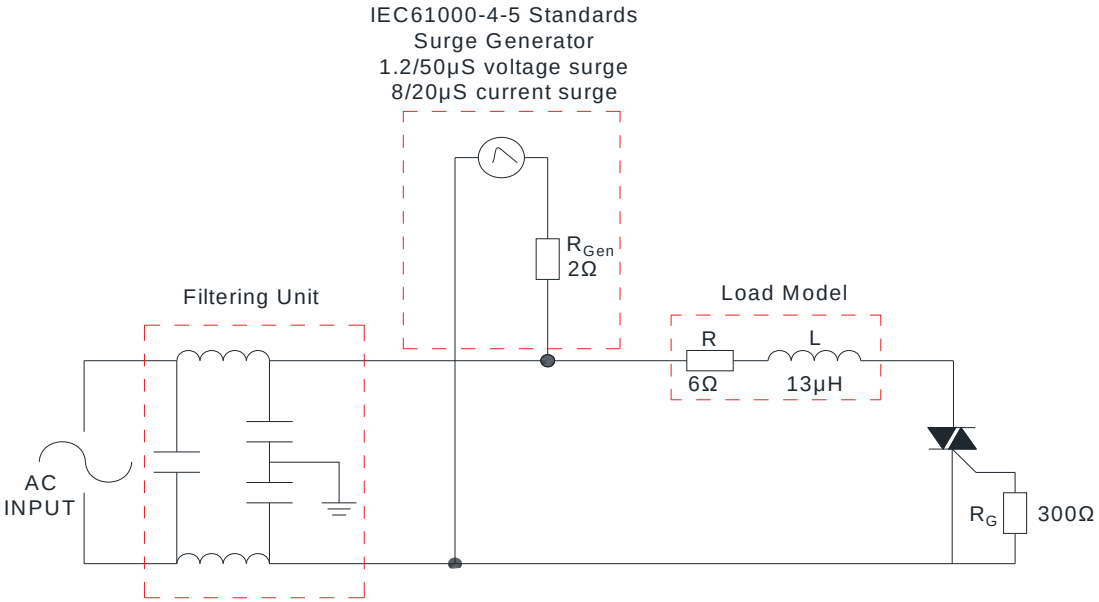
J	ST	08	F	-800	BW
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}$:8A	F:TO-220F(Ins)	800:V_{DRM} /V_{RRM} ≥ 800V	BW:I_{GT1-3} ≤ 50mA

MARKING



JST08F-800BW

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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